

UM2366/UM2366A

8K \times 8 NMOS ROM



Featurés

- 2765 EPROM pin compatible
- 8192 x 8 bit organization
- Single + 5 volt supply
- Access time 200/300/450 ns (max)
- Totally static operation
- Completely TTL compatible
- 28 Pin JEDEC approved pinout

Description

The UM2366 and UM2366A high performance Read Only Memories are organized 8192 words by 8 bits with access times from 200 ns to 450 ns. The ROMs are designed to be compatible with all microprocessor and similar applications where high performance, large bit storage and simple interfacing are important design considerations. Both ROMs conform to the JEDEC approved pinout for 28 pin 64K ROMs.

The UM2366 offers the simplest operation (no power down.) Its four programmable chip selects allow up to sixteen 64K ROMs to be OR-tied without external decoding.

The UM2366A offers an automatic power down feature.

- UM2366A automatic power down (CE)
 - output enable function (\overline{OE})
 - two programmable chip selects (CS)
 - UM2366 non power down version
 - four programmable chip selects (CS)
- Three state outputs for wire-or expansion
- EPROMs accepted as program data input

Power down is controlled by the Chip Enable $\overline{(CE)}$ input. When \overline{CE} goes high, the device will automatically power down and remain in a low power standby mode as long as \overline{CE} remains high. This unique feature provides system level power savings as much as 90%. An additional feature of the UM2366A is the Output Enable $\overline{(OE)}$ function. This eliminates bus contention in multiple bus microprocessor systems. The two programmable Chip Selects (CS) allow up to four 64K ROMs to be OR-tied without external decoding.

Both the UM2366 and UM2366A are pin compatible with the 2764 EPROM thus eliminating the need to redesign printed circuit boards for volume mask programmed ROMs after prototyping with EPROMs.





Absolute Maximum Ratings*

Temperature Under Bias
Storage Temperature
Voltage on Any Pin with Respect to Ground
Power Dissipation

D.C. Characteristics

 $= 0^{\circ}C + 20^{\circ}C + 10^{\circ}C$ - (5) + 100() *Comments

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent demage to the device. These are stress ratings only. Functional operation of this device at these or any other conditions above those indicated on the operational sections of this specification is not implied and exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
V _{OH}	Output HIGH Level	2.4		Vcc	V	I _{OH} = -1.0 mA
Vol	Output LOW Level			0.4	V	I _{OL} = 3.2 mA
VIH	Input HIGH Level	2.0	,	Vcc	V	
VIL	Input LOW Level	-0.5		0.8	V	
LI	Input Leakage Current			10	μA	$V_{IN} = OV \text{ to } V_{CC}$
LO	Output Leakage Current			10	μA	V _{OUT} = OV to V _{CC}
¹ cc	Operating Supply Current			100	mA	Note 1
I _{SB}	Standby Supply Current			12	mA	Note 2
los	Output Short Circuit Current			70	mA	Note 3

Capacitance

 $(T_A = 25^{\circ}C, f = 1.0 \text{ MHz})$

Symbol	Parameter	Min.	Max.	Unit	Conditions	
C ₁	Input Capacitance		5	pf	V _{IN} = OV	
CO	Output Capacitance		5	pf	V _{OUT} = 0V	

Note: This parameter is periodically sampled and is not 100% tested.

A.C. Characteristics

 $(T_A = 0^{\circ}C \text{ to } + 70^{\circ}C, V_{CC} = +5V \pm 10\%)$ (Note 7)

Symbol	Parameter	UM2366-2 UM2366A-2		UM2366-1 UM2366A-1		UM2366 UM2366A		Unit	Condition
		Min.	Max.	Min.	Max.	Min.	Max.	1	
tCYC	Cycle Time	200		300		450		ns	
t _{AA}	Address Access Time		200		300		450	ns	
^t он	Output Hold After Address Change	10		10	-	10		ns	
^t ACE	Chip Enable Access Time		200		300		450	ns	Note 4
t _{ACS}	Chip Select Access Time		85		100	1	150	ns	
t _{AOE}	Output Enable Access Time		85		100		150	ns	Note 4
t _{LZ}	Output LOW Z Delay	10		.10		10		ns	Note 5
^t HZ	Output HIGH Z Delay		85		100		150	ns	Note 6
t _{PU}	Power Up Time	0		0		0		ns	Note 4
t _{PD}	Power Down Time		85		100		150	ns	Note 4

Notes:

Measured with device selected and outputs unloaded.
Applies to "A" versions only and measured with CE = 2.0V.

For a duration not to exceed one second.
Applies to "A" versions (power down) only.

Output low impedance delay (t_{LZ}) is measured from CE and OE going low and CS going active, whichever occurs last.
Output high impedance delay (t_{HZ}) is measured from either CE or OE going high or CS going inactive, whichever occurs

first. 7. A minimum 0.5 ms time delay is required after application of V_{CC} (+5V) before proper device operation is achieved.



Timing Diagrams

Propagation Delay from Address ($\overline{CE} = \overline{OE} = LOW$, $CS/\overline{CS} = Active$)



Propagation Delay from Chip Enable, Chip Select (Address Valid)



A.C. Testing Input, Output Waveform



A.C. Testing Load Circuit



Programming Instructions

All UMC Read Only Memories (ROM) utilize computer aided techniques to manufacture and test custom bit patterns. The customer's bit pattern and address information can be supplied to UMC in a number of different ways. UMC can process customer inputs in EPROM, ROM, PROM, paper tape, and computer punched cards. Contact your UMC sales representative for complete details on each of the various data input formats.

Programming instructions are listed at the end of the Memory Section.

Ordering Information

Part	Access	Operating	Standby	Package
Number	Time	Current	Current	Type
UM2366 UM2366-1 UM2366-2 UM2366A UM2366A-1 UM2366A-2	450 ns 300 ns 200 ns 450 ns 300 ns 200 ns	100 mA 100 mA 100 mA 100 mA 100 mA 100 mA	N.A. N.A. 12 mA 12 mA 12 mA	Plastic Plastic Plastic Plastic Plastic Plastic